

ABSTRACT

Disclosed are a process of manufacturing a thin-film transistor sheet and a thin-film transistor sheet manufactured by the process, the process comprising the steps of providing a gate busline on a substrate, providing, on the surface of the substrate on the gate busline side, an insulation layer capable of receiving a fluid electrode material, supplying the fluid electrode material to the insulation layer, the fluid electrode material being allowed to permeate the insulation layer, forming a gate electrode from the permeated fluid electrode material to be in contact with the gate busline, forming a gate insulating layer on the gate electrode, and forming a semiconductor layer on the gate insulating layer.